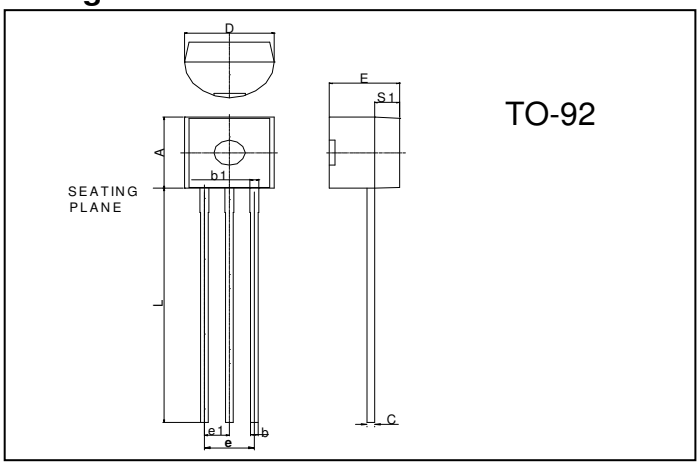
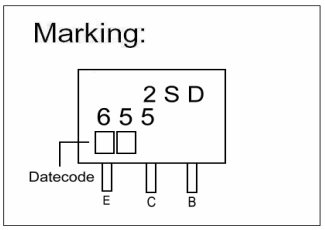
G2SD655 Silicon NPN Epitaxial

Application

Low frequency power amplifier, Muting.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings (Ta = 25℃)

Parameter		Ratings	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	15	V
Emitter to Base Voltage	V_{EBO}	5	V
Collect Current(DC)	I_C	0.7	A
Collect peak current	$I_{C(peak)}$	1.0	A
Junction Temperature	Tj	+150	℃
Storage Temperature Range	Tstg	-55 ~ +150	℃
Total Power Dissipation	P_D	500	mW

Electrical Characteristics(Ta = 25℃)

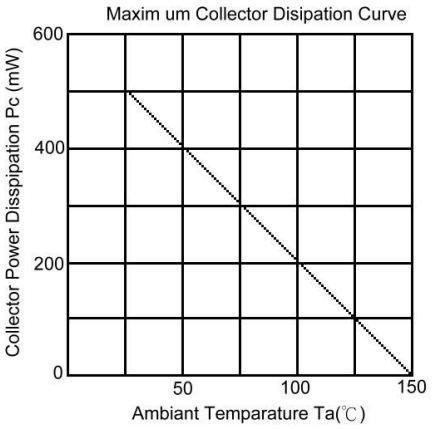
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	30	-	-	V	I_C=10uA ,I_E=0
BV_{CEO}	15	-	-	V	I_C=1mA,R_{BE}=∞
BV_{EBO}	5	-	-	V	I_E=10uA,I_C=0
I_{CBO}	-	-	1.0	uA	V_{CB}=20V, I_E=0
V_{BE}	-	-	1.0	V	V_{CE}=1V,I_C=150mA
VCE(sat)	-	0.15	0.5	V	I_C=500mA, I_B=50mA *2
h_{FE}1 *1	250	-	1200		V_{CE}=1V, I_C=150mA *2
fT	-	250	-	MHz	V_{CE}=1V, I_C=150mA

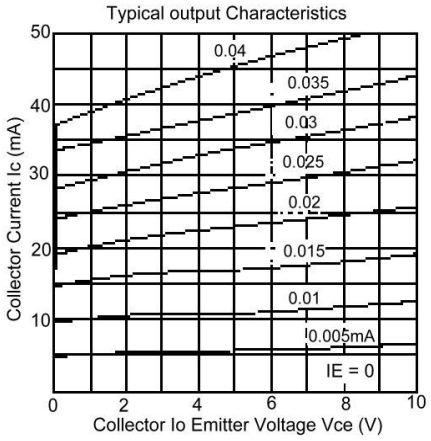
Notes: 1. The G2SD655 is grouped by h_{FE} as follows.
2. Pulse test

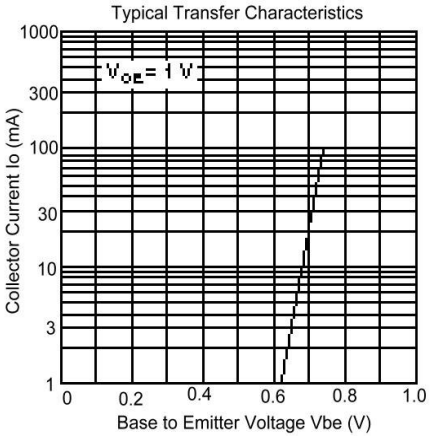
Classification of Rank

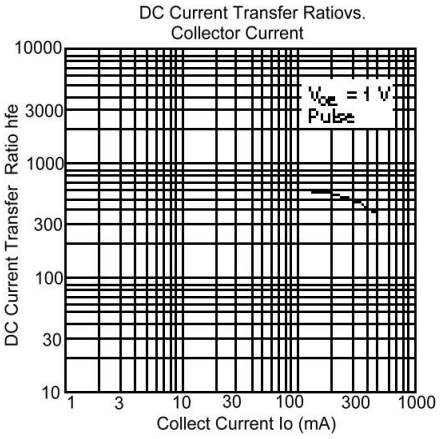
Rank	D	E	F
Range	250-500	400-800	600-1200

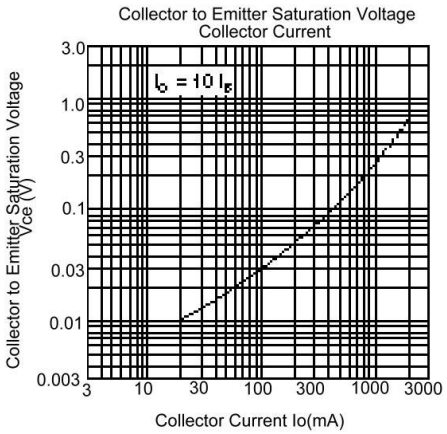
Characteristics Curve

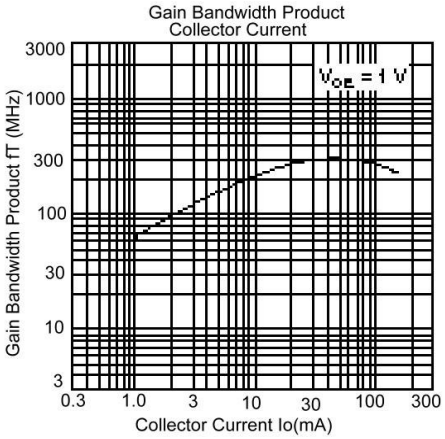


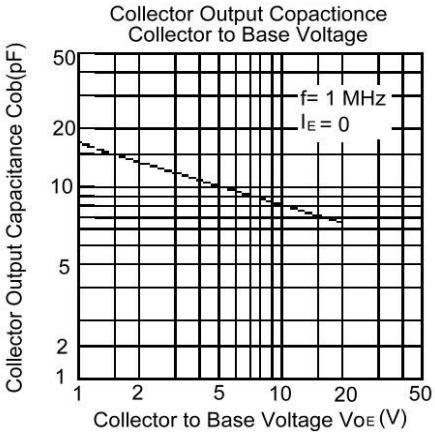












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